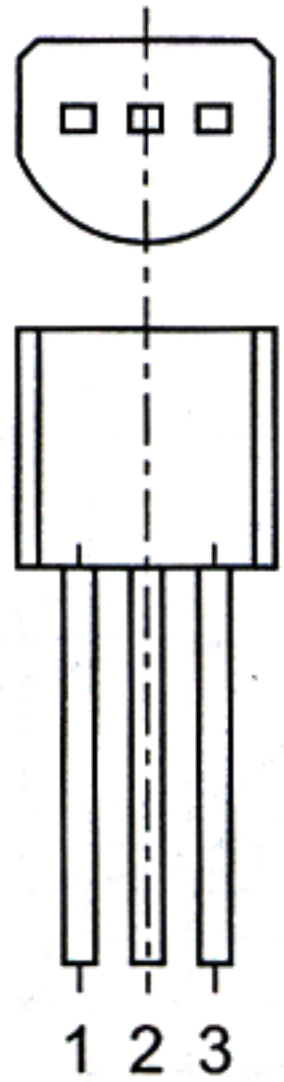


TO-92 Plastic-Encapsulate Transistors

MPS2907A TRANSISTOR(PNP)



TO-92

1.EMITTER

2.BASE

3.COLLECTOR

FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.6 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

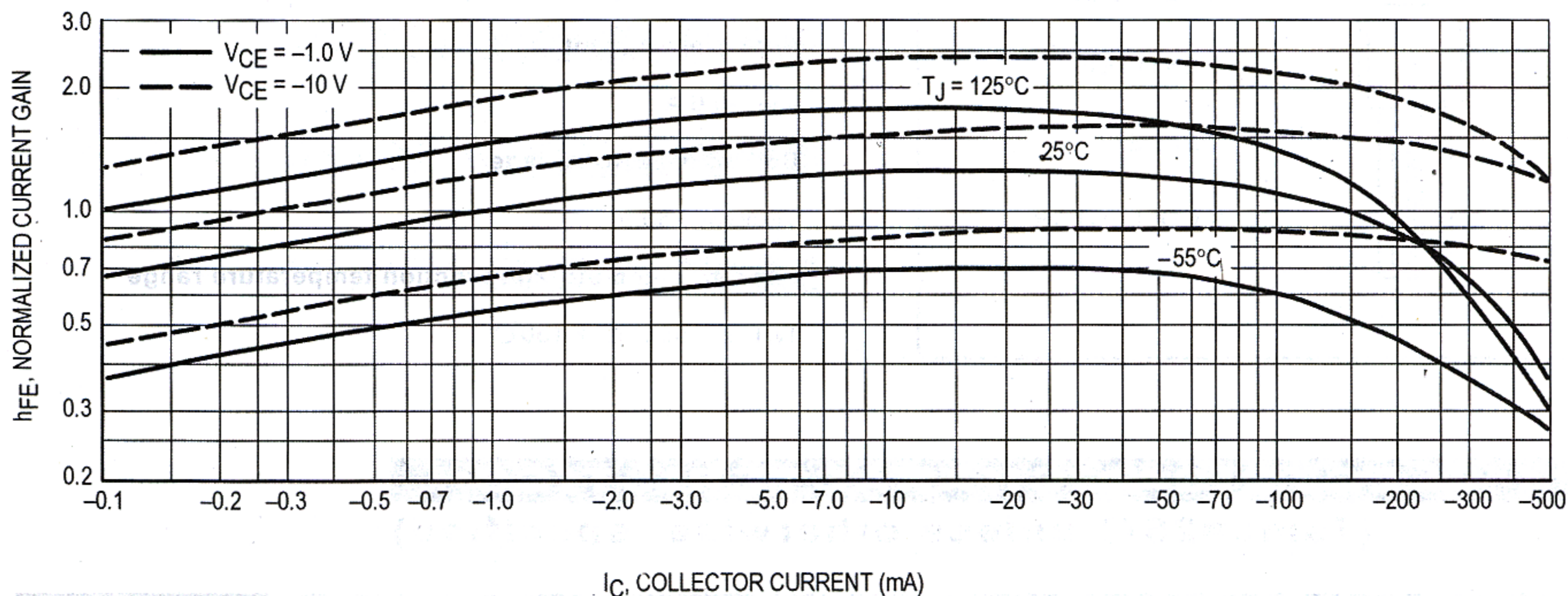
ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

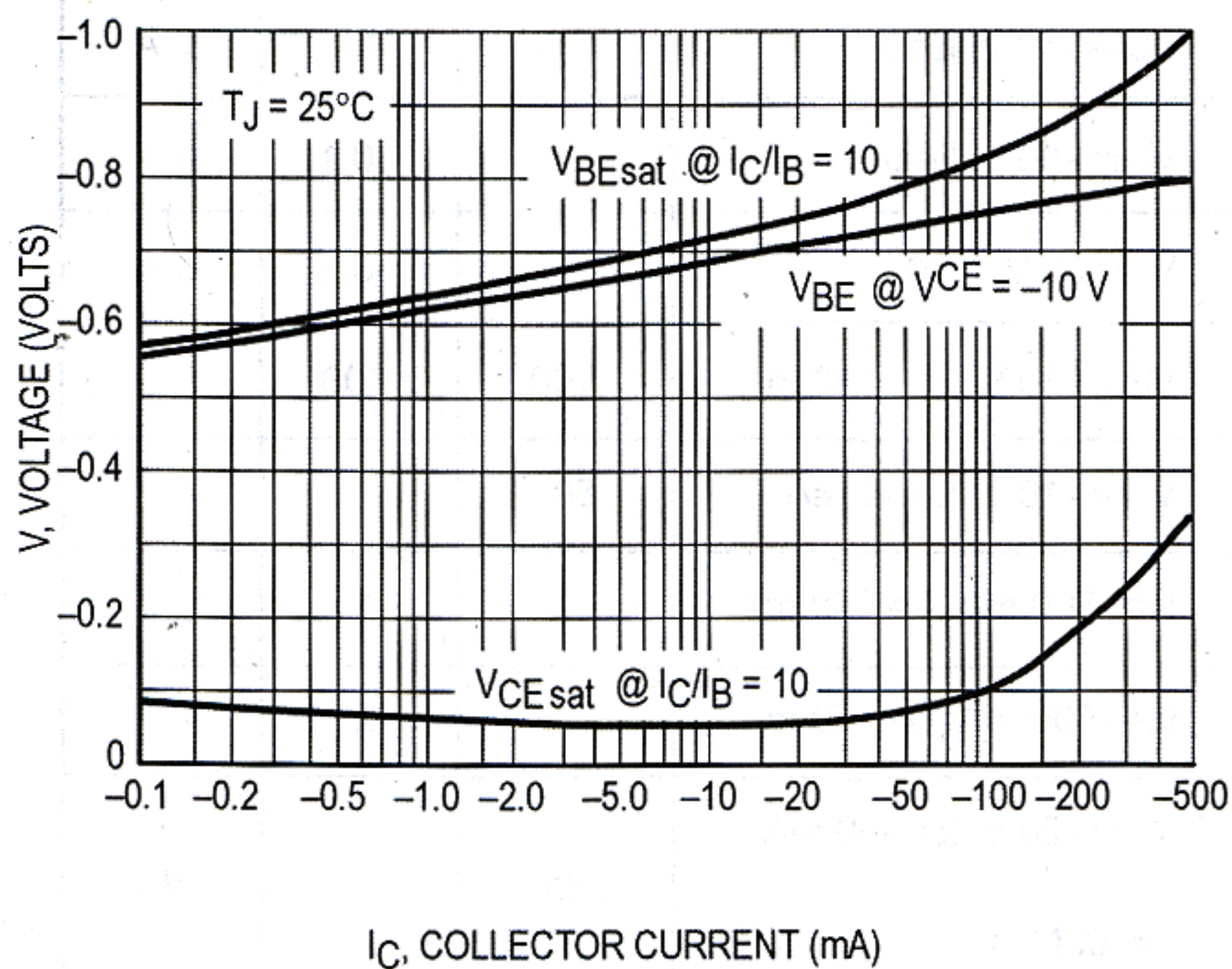
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 mA, I_B = 0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50 V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -50 V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3 V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10 V, I_C = -150 mA$	100	300	
	$h_{FE(2)}$	$V_{CE} = -10 V, I_C = -1 mA$	60		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -500 mA, I_B = -50 mA$		-1	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -500 mA, I_B = -50 mA$		-2	V
Transition frequency	f_T	$V_{CE} = -20 V, I_C = -50 mA$ $f = 100 MHz$	200		MHz

CLASSIFICATION OF $h_{FE(1)}$

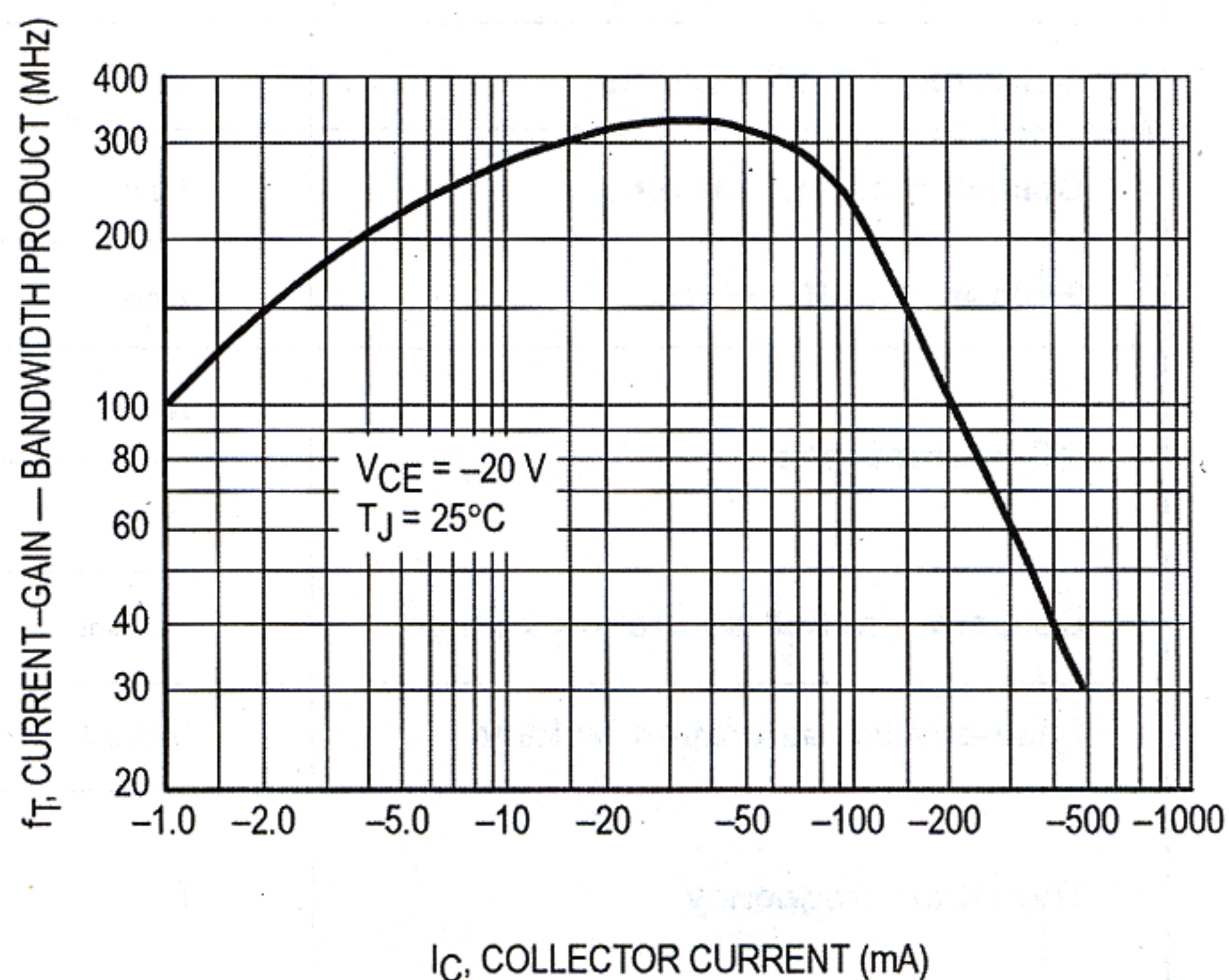
Rank	L	H
Range	100-200	200-300



DC Current Gain



"On" Voltage



Current-Gain — Bandwidth Product